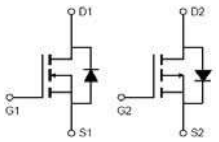
N&P-Channel complementary Power MOSFET

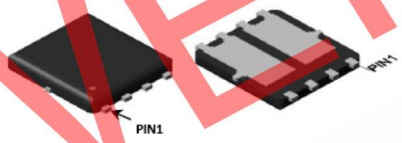
Description

The AP3910GD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.



Schematic diagram

Marking and pin assignment



Top View Bottom View

General Features

N channel

- V_{DS} =30V,I_D =36A
  $R_{DS(ON)}$ <12mΩ @ V_{GS}=10V
  $R_{DS(ON)}$ <15mΩ @ V_{GS}=4.5V

p channel

- V_{DS} =-30V,I_D =-30A
  $R_{DS(ON)}$ <14mΩ @ V_{GS}=-10V
  $R_{DS(ON)}$ <20mΩ @ V_{GS}=-4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- H-bridge
- Inverters

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3910GD	AP3910GD	PDFN5*6-8L		-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	30	-30	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Continuous Drain Current	T_C=25℃	I_D	36	-30	A
	T_C=100℃		22.8	-20.2	
Pulsed Drain Current (Note 1)		I_{DM}	90	-80	A
Maximum Power Dissipation	T_C=25℃	P_D	35		W
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150		℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	3.6	℃/W

N&P-Channel complementary Power MOSFET

N-Channel Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1	1.3	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=10A	-	9.5	14	mΩ
		V_{GS}=4.5V, I_D=5A	-	11	20	
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=10A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=15V,V_{GS}=0V, F=1.0MHz	-	790	-	PF
Output Capacitance	C_{oss}		-	225	-	PF
Reverse Transfer Capacitance	C_{rss}		-	160	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=25V,I_D=1A V_{GS}=10V,R_{GEN}=6Ω	-	30	-	nS
Turn-on Rise Time	t_r		-	20	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	100	-	nS
Turn-Off Fall Time	t_f		-	80	-	nS
Total Gate Charge	Q_g	V_{DS}=15V,I_D=10A, V_{GS}=5V	-	13	-	nC
Gate-Source Charge	Q_{gs}		-	5.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=10A	-	-	1.2	V

N&P-Channel complementary Power MOSFET

N- Channel Typical Electrical and Thermal Characteristics (Curves)

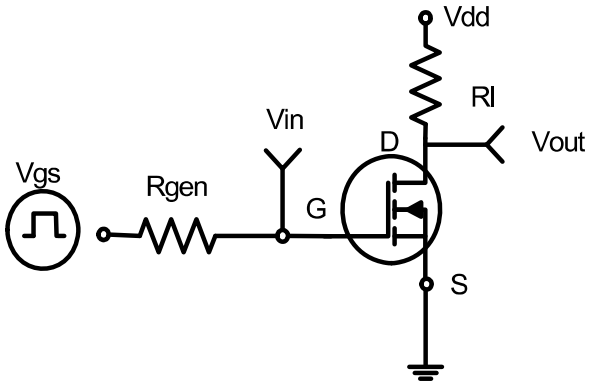


Figure 1:Switching Test Circuit

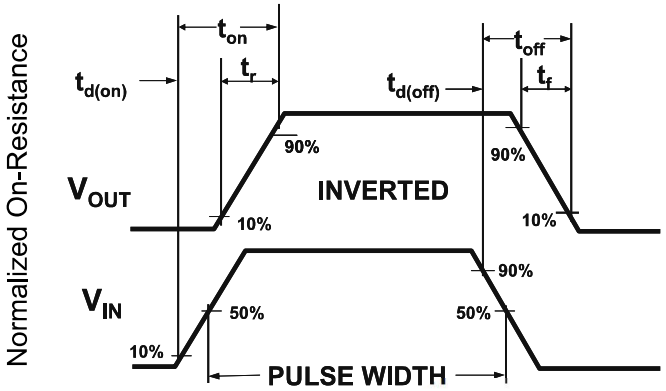


Figure 2:Switching Waveforms

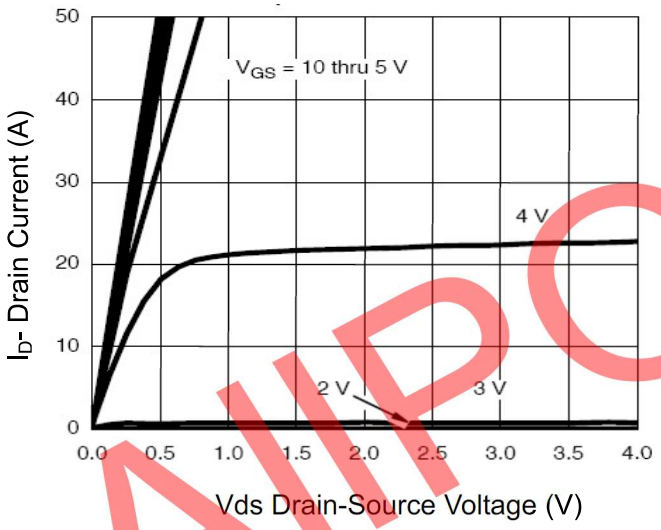


Figure 3 Output Characteristics

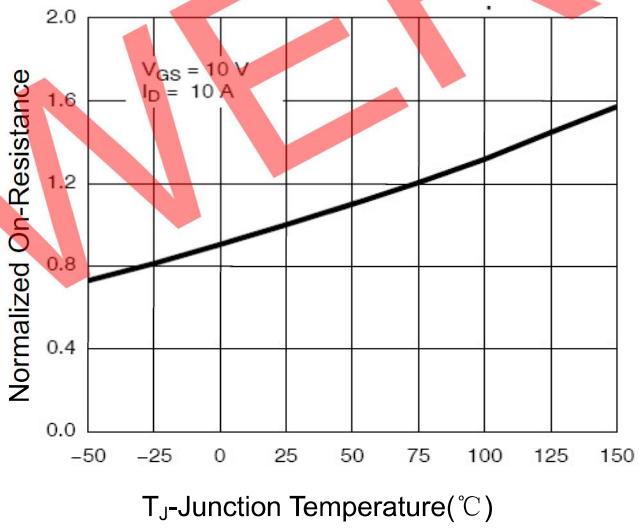


Figure 4 Rdson-JunctionTemperature

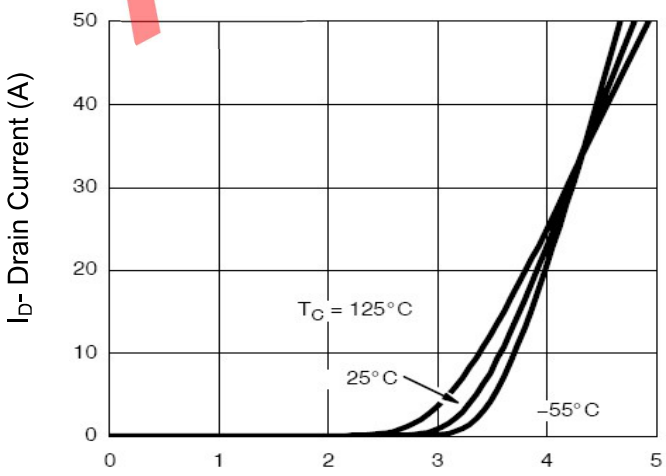


Figure 5 Transfer Characteristics

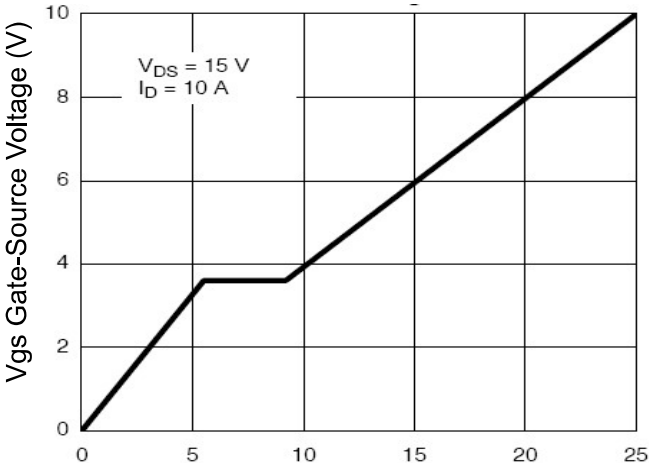


Figure 6 Gate Charge

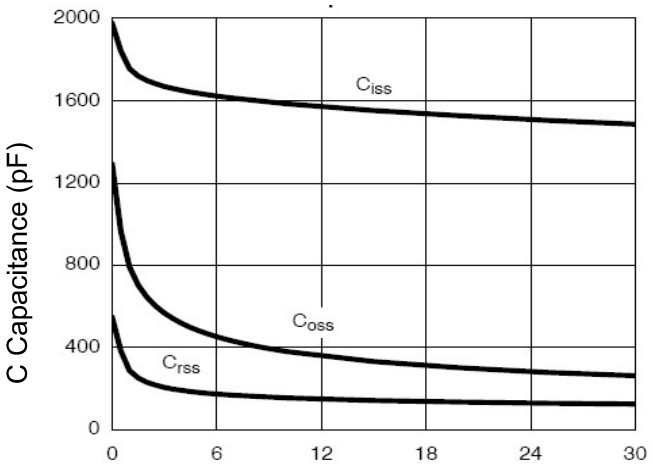


Figure 7 Capacitance vs Vds

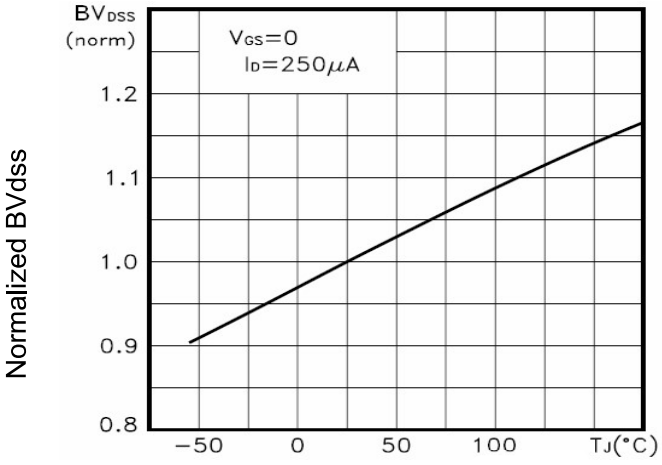


Figure 8 BV_{DSS} vs Junction Temperature

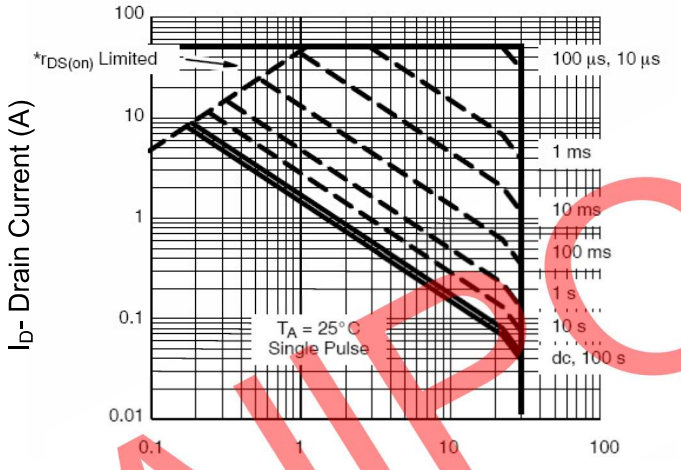


Figure 9 Safe Operation Area

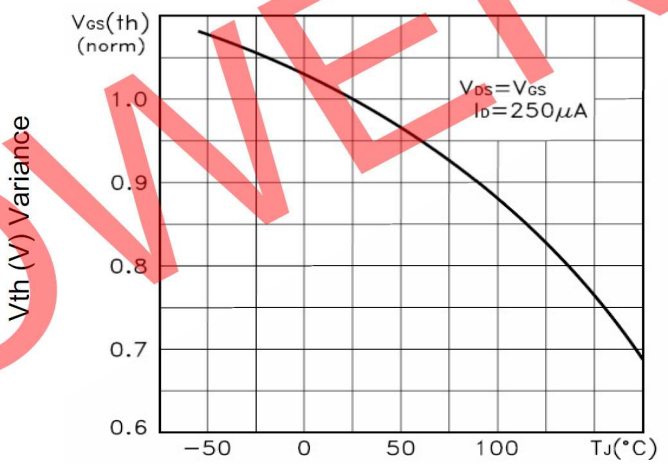


Figure 10 $V_{GS(th)}$ vs Junction Temperature

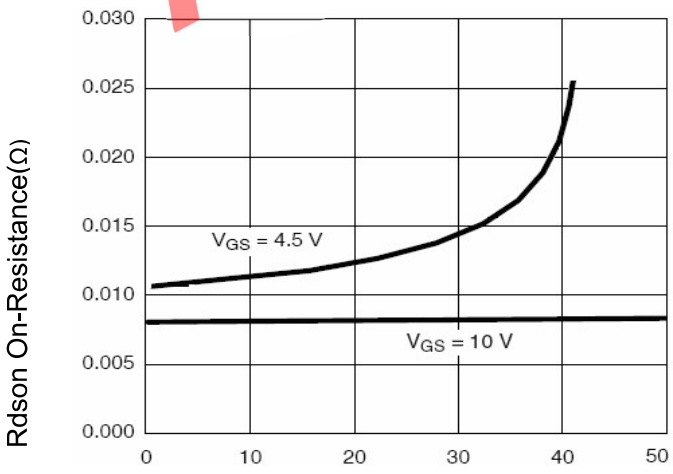


Figure 11 Rdson- Drain Current

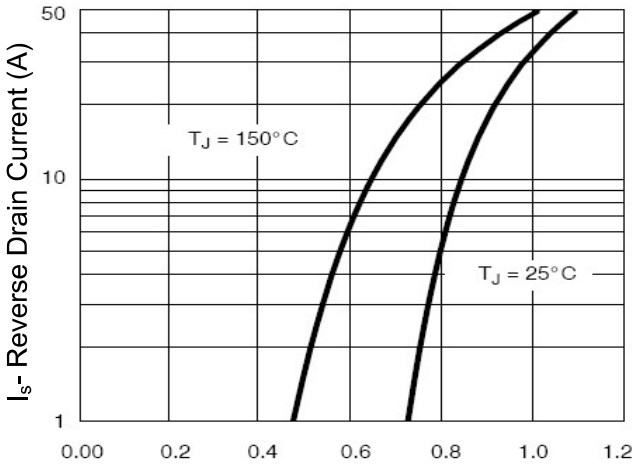


Figure 12 Source- Drain Diode Forward

P-Channel Electrical Characteristics (T_C=25℃unless otherwise noted)

Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.0	-1. 5	-2.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-15A	-	11	14	m Ω
		V_{GS}=-4.5V, I_D=-10A	-	15.5	20	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-15A	30	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-15V,V_{GS}=0V, F=1.0MHz	-	2800	-	PF
Output Capacitance	C_{oss}		-	410	-	PF
Reverse Transfer Capacitance	C_{rss}		-	280	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-15V, ID=-10A, V_{GS}=-10V,R_{GEN}=3Ω	-	15	-	nS
Turn-on Rise Time	t_r		-	11	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	44	-	nS
Turn-Off Fall Time	t_f		-	21	-	nS
Total Gate Charge	Q_g	V_{DS}=-15V,I_D=-10A,V_{GS}=-10V	-	48	-	nC
Gate-Source Charge	Q_{gs}		-	12	-	nC
Gate-Drain Charge	Q_{gd}		-	14	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-2A	-	-	-1.2	V

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

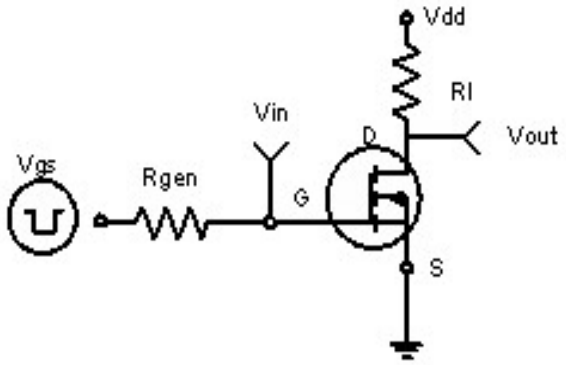


Figure 1 Switching Test Circuit

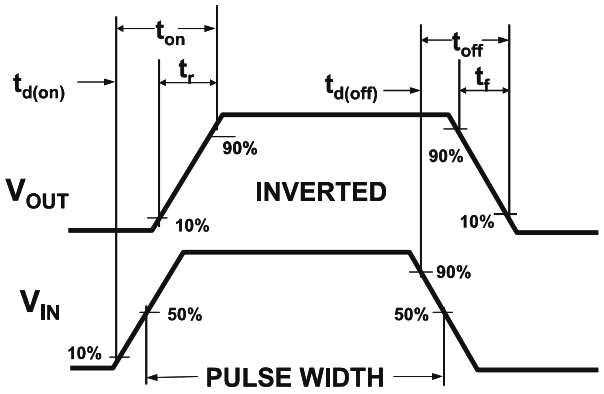


Figure 2 Switching Waveforms

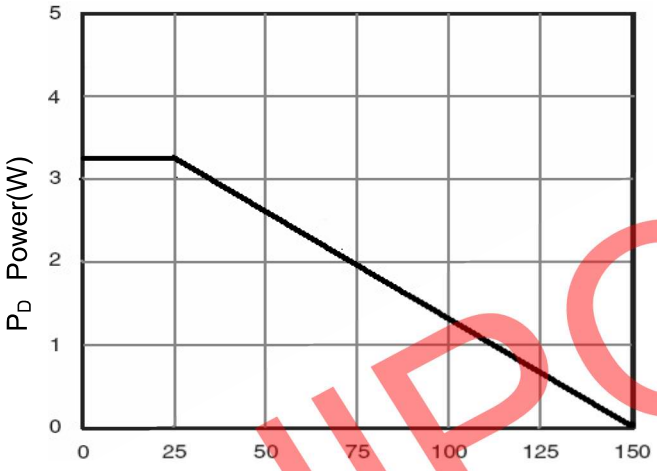


Figure 3 Power Dissipation

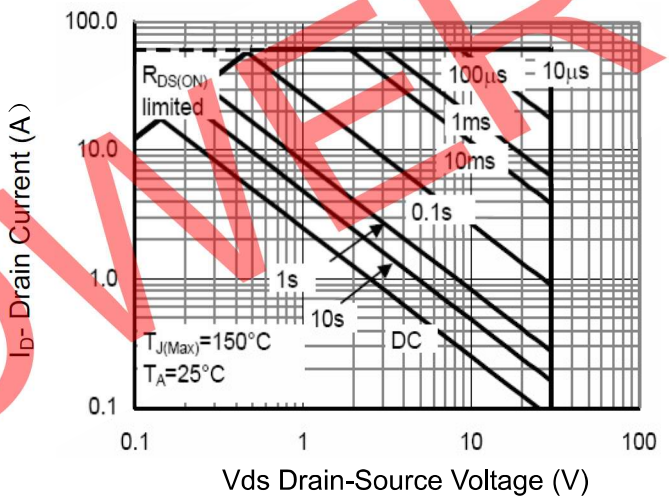


Figure 4 Safe Operation Area

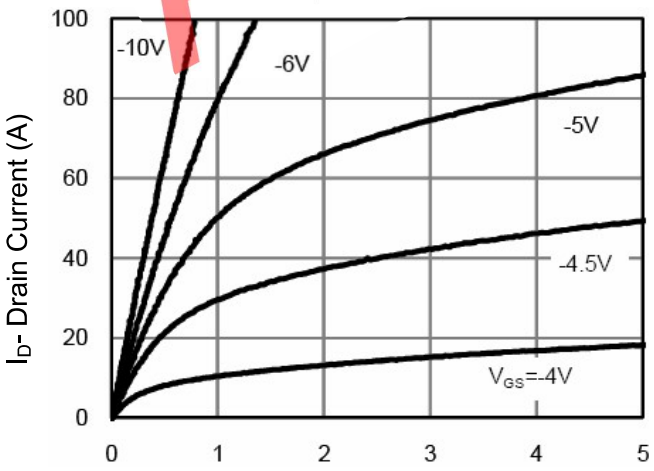


Figure 5 Output Characteristics

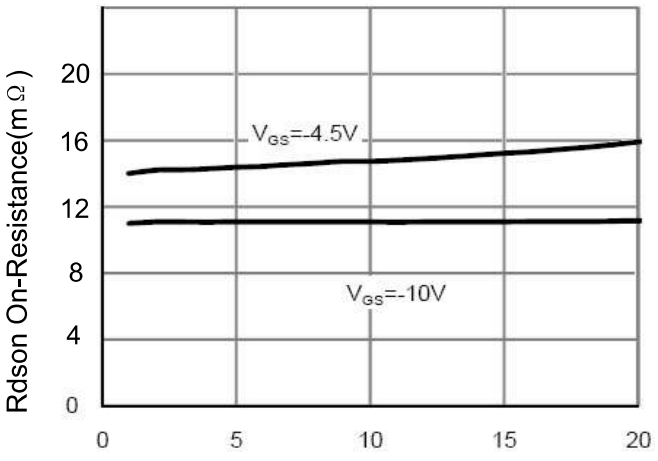


Figure 6 Drain-Source On-Resistance

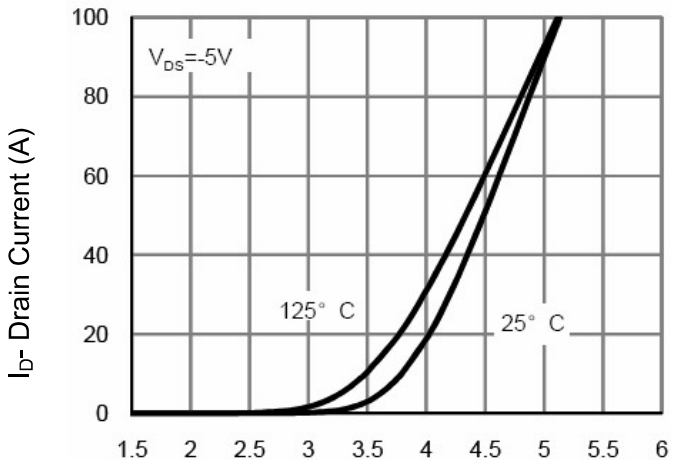


Figure 7 Transfer Characteristics

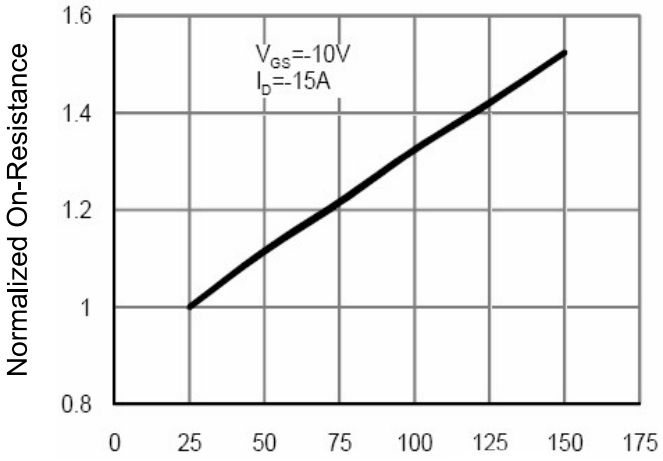


Figure 8 Drain-Source On-Resistance

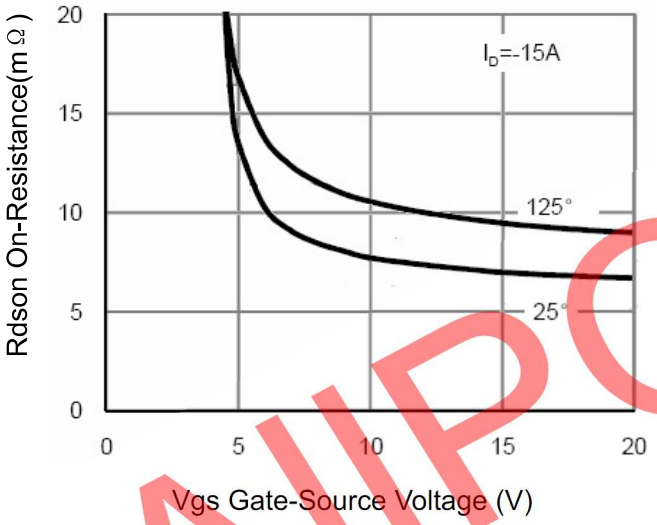


Figure 9 Rdson vs Vgs

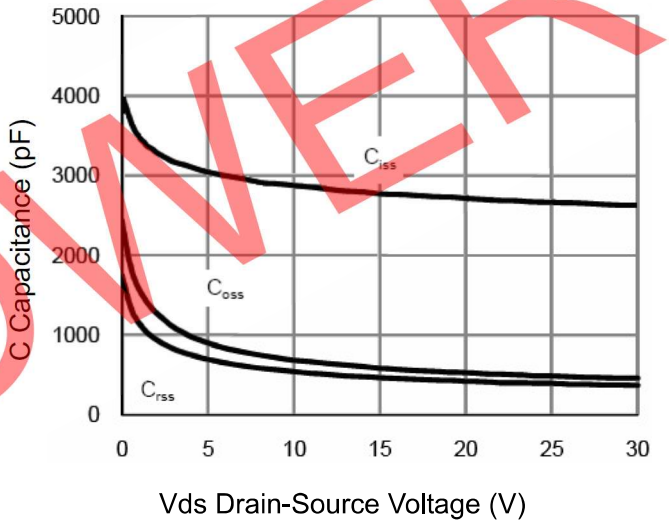


Figure 10 Capacitance vs Vds

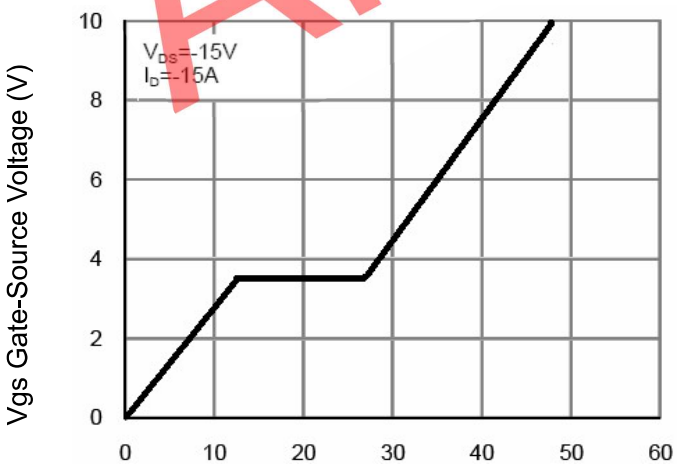


Figure 11 Gate Charge

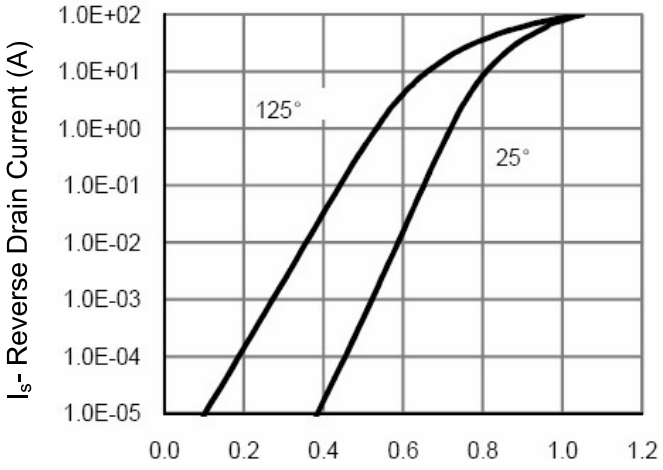
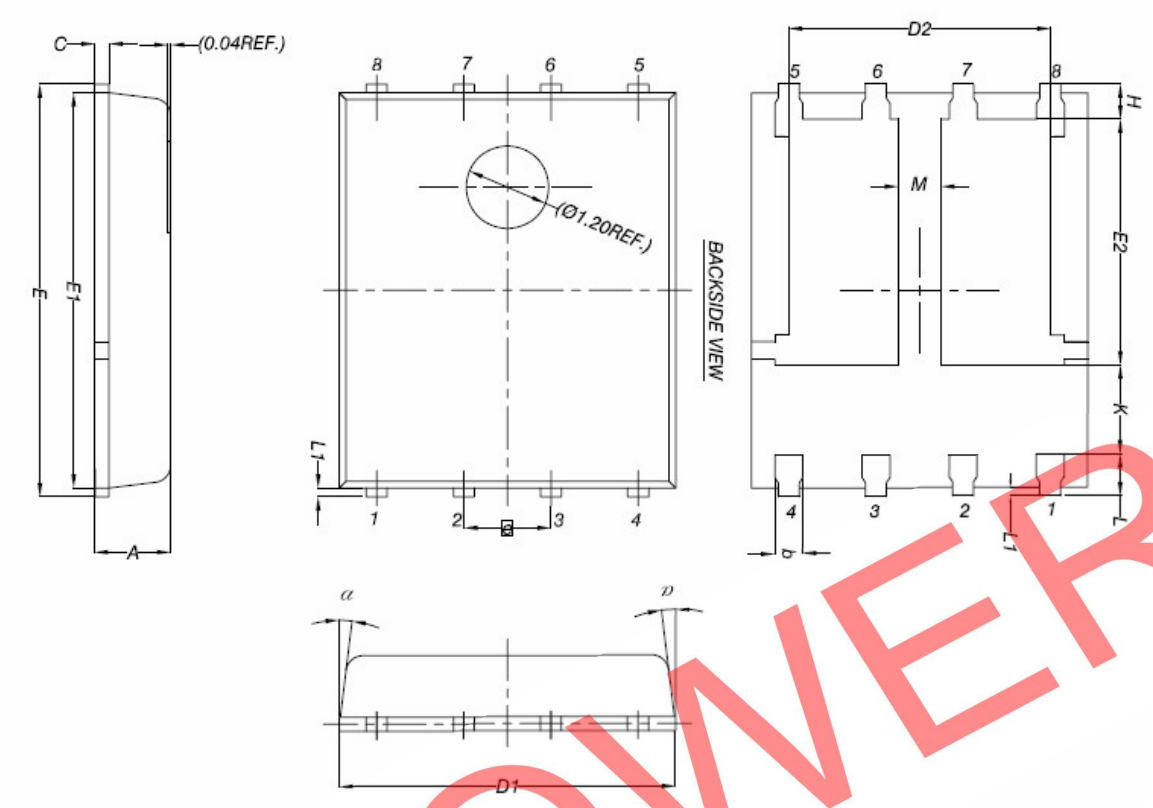


Figure 12 Source- Drain Diode Forward

N&P-Channel complementary Power MOSFET

DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
M	0.50	-	-
α	0°	-	12°